Room-temperature continuous-wave operation of long wavelength (λ = 9.5 μm) MOVPE-grown quantum cascade lasers


High-power continuous-wave operation of long wavelength quantum cascade lasers grown by metal organic vapour phase epitaxy is reported. The lasers have been processed as buried heterostructures with thick gold-plated contacts. The devices emit at a wavelength of 9.5 μm with output powers of several hundreds of milliwatts at room temperature.

Fabrication and measurement techniques: The structure was grown by MOVPE with the following layer sequence. Thirty-five periods of a 2-Phonon design [8] active region are used as the active core and sandwiched between two 0.5 μm-thick n-doped (1.5 x 10^16 cm⁻³) In₀.₅Ga₀.₄7As layers. The upper cladding layers consist of 3.5 μm-thick n-doped (5 x 10^16 cm⁻³) InP, followed by a 0.5 μm-thick n-doped (2.5 x 10^16 cm⁻³) InP cap layer. The lower cladding consists of a 3.5 μm-thick n-doped (5 x 10^16 cm⁻³) InP layer grown on a highly doped substrate (3 x 10^18 cm⁻³). The average doping in the active region is 8.1 x 10^15 cm⁻³. The waveguide loss is calculated to be γₔ = 6 cm⁻¹ and the confinement factor Γ = 0.5.

Buried heterostructure lasers were processed using conventional fabrication techniques [9]. Ridges with a width of either 9 or 13 μm were fabricated by wet etching. Fe-doped InP was then regrown to planarise the structure, helping to decouple laterally. The optical mode is formed by the lossless metal contacts and to lower the thermal resistance of the device while minimising leakage currents. Electrical contacts are provided by Ti/Au metalisation evaporated directly onto the n-InGaAs capping layer and the Fe:InP surrounding the laser ridge. An additional 5 μm-thick gold layer was subsequently electroplated on the top contact to further improve heat dissipation. The devices were cleaved and the cleaved facets were left uncoated. For pulsed measurements, the devices were mounted ridge side up onto copper blocks and wire bonded. For CW measurements, the devices were mounted epi-down side down. The 3 mm-long cavity devices were mounted epi-down on copper blocks with indium solder using traditional methods.

The 3 mm-long devices were measured under active temperature control, where the temperature was stabilised using a water-cooled heatsink. The longer cavity devices were temperature controlled in a passive manner by means of a constant temperature, water-cooled heatsink to which the device mounts were attached. Optical power measurements were performed with a calibrated large area thermopile detector positioned as close to the output facet of the device as possible. No correction was introduced for collection efficiency.

Characterisation: Fig. 1a shows the power (80 kHz, 125 ns) VI-characteristics of 9 μm-wide devices and a 3 mm-long device at room temperature (295 K). Additionally, the LI-characteristics of devices with different dimensions are shown. The emission wavelength at RT is 9.5 μm (see inset of Fig. 1b).

The slope efficiency decreases from 380 mW/A for a 3 mm-long device to 242 mW/A (272 mW/A) for a 7 mm (5 mm)-long device owing to decreasing mirror losses. The decreasing threshold with increasing length is a manifestation of the reduced mirror losses. From this dependence, we can deduce the waveguide losses and the modal gain coefficient. Fig. 1b shows the threshold current density against the inverse of the length of the devices. A linear fit gives a modal gain coefficient of 8.5 cm/kA and waveguide losses of 10.7 cm⁻¹. The measured losses are higher than those obtained with a two-dimensional simulation. The simulation, however, only includes losses due to free-carrier absorption and neglects optical losses caused by intersubband absorption in the injector and scattering losses. One scattering mechanism is sidewall scattering along the laser ridge. It depends on the width of the devices and the Fe:InP coating. Fig. 1d shows the waveguide losses for devices with different ridge widths and lengths (solid line: 9 μm-wide devices; dashed line: 3 mm-long and 13 μm-wide device). For 3 mm-long and 9 μm-wide device VI curve also shown.

Fig. 1 Output power against current characteristics for devices with different ridge widths and lengths, and measured pulsed threshold current density against reciprocal cavity length at 295 K

a Output power against current characteristics for devices with different ridge widths and lengths (solid line: 9 μm-wide devices; dashed line: 3 mm-long and 13 μm-wide device). For 3 mm-long and 9 μm-wide device VI curve also shown.

b Measured pulsed threshold current density against reciprocal cavity length at 295 K.

Solid line is result of linear least squares fit.

Inset: Spectrum of this device at room temperature (pulsed operation)
3 mm-long device to 1.65 kA/cm² for a 13 μm-wide device with the same length. This corresponds to a decrease in waveguide losses of about 1 cm⁻¹. Although narrower ridges have slightly higher losses, buried heterostructures have the advantage that the refractive index change between the active area and the overgrown material is very small, which reduces significantly the losses due to sidewall scattering compared to conventional ridge waveguide designs with insulator/metal sidewalls. Further improvements of our devices are expected by decreasing the doping in the waveguide layers as this significantly decreases the free-carrier absorption losses at longer wavelength. Recent work on long wavelength QCLs has shown that the losses due to free-carrier absorption can further be reduced without significantly increasing the series resistance [2].

The devices were also tested in CW operation (Fig. 2). A 3 mm-long and 9 μm-wide device had a threshold current density of 1.9 kA/cm² and a slope efficiency of 245 mW/A. The maximum output power for this device per facet was 48 mW at a current density of 2.6 kA/cm². We further tested a 5 mm-long and 13 μm-wide device in CW operation. The threshold current density for this device at RT was as low as 1.54 kA/cm². The output power per facet for this device is 180 mW at RT and 220 mW at 14 °C. This corresponds to a wall-plug efficiency of 1.9% (2.3%) if one includes the output for both facets 360 mW (440 mW) at RT (14 °C).

![Graph showing L-I characteristics of devices with different length and width operated in continuous wave (facets of devices left uncoated)](image)

**Fig. 2** L-I characteristics of devices with different length and width operated in continuous wave (facets of devices left uncoated)

**Conclusion:** We have demonstrated high performance QCLs grown by MOVPE operating at 9.5 μm. The performance of these devices is comparable to the best devices grown by MBE. Further improvements in bandstructure engineering and waveguide design, especially by further decreasing the doping in the waveguide layers, should make the high-power CW operation of MOVPE-grown QCLs feasible in the whole atmospheric window range (up to 13 μm).

**Acknowledgement:** The authors acknowledge financial support from NIST’s Advanced Technology Program under contract 70NANB3H3026.

© The Institution of Engineering and Technology 2007
25 July 2007
Electronics Letters online no: 20072162
doi: 10.1049/el:20072162

C. Pfügl, L. Diehl and F. Capasso (Harvard School of Engineering and Applied Sciences, Harvard University, Cambridge, MA 02138, USA)

E-mail: pfugl@seas.harvard.edu

A. Tsekoun, R. Go and C.K.N. Patel (Pranalitica, Inc., 11101 Colorado Avenue, Santa Monica, CA 90401, USA)

X. Wang, J. Fan and T. Tanbun-Ek (Adtech Optics, Inc., 18007 Cortney Court, City of Industry, CA, 91748, USA)

C.K.N. Patel: Also with the Department of Physics & Astronomy, University of California, Los Angeles, CA, 90095, USA

**References**


